



FINAL PRODUCT/PROCESS CHANGE NOTIFICATION #20349

Generic Copy

Issue Date: 20-Jun-2014

TITLE: Qualification of Niigata Fab (Japan) as the additional wafer source for Bipolar Power Planar Transistors.

PROPOSED FIRST SHIP DATE: 20-Sep-2014

AFFECTED CHANGE CATEGORY(S): ON Semiconductor Fab Site

FOR ANY QUESTIONS CONCERNING THIS NOTIFICATION:

Contact your local ON Semiconductor Sales Office or CW Yong <chuenwai.yong@onsemi.com>

SAMPLES: Contact your local ON Semiconductor Sales Office

ADDITIONAL RELIABILITY DATA: Available

Contact your local ON Semiconductor Sales Office or Laura Rivers <laura.rivers@onsemi.com>

NOTIFICATION TYPE:

Final Product/Process Change Notification (FPCN)

Final change notification sent to customers. FPCNs are issued at least 90 days prior to implementation of the change.

ON Semiconductor will consider this change approved unless specific conditions of acceptance are provided in writing within 30 days of receipt of this notice. To do so, contact <quality@onsemi.com>.

DESCRIPTION AND PURPOSE:

This is the Final Notification by ON Semiconductor notifying customers of its plan to add Niigata Fab (Japan) as the qualified wafer source for Bipolar Power Planar Transistor.

The Niigata Fab facility is an ON Semiconductor owned wafer fab that has been producing products for ON Semiconductor. Several existing technologies within ON Semiconductor's product families are currently sourced from Niigata Fab. ON Semiconductor Niigata Wafer Fab is an internal factory that is TS16949, ISO-9001 and ISO-14000 certified.

Qualification tests are designed to show that the reliability of the transferred devices will continue to meet or exceed ON Semiconductor standards.



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RELIABILITY DATA SUMMARY:

Package: TO220

MJE5852G

Test:	Conditions:	Interval:	Results
HTRB	Ta=150C,80% Rated Voltage	1008 hrs	0/80
Autoclave	Ta=121C RH=100% ~15 psig	96 hrs	0/80
H3TRB	Ta=85C RH=85% bias=80% rated V or100V Max	1008 hrs	0/80
IOL	Ta=25C, Delta TJ = 100 C, Ton/off = 3.5 min.	8572 cyc	0/80
TC	Ta= -65 C to 150 C	1000 cyc	0/80
RSH	Ta=260C, 10 sec dwell		0/30

Package: DPAK

MJD340T4G

Test:	Conditions:	Interval:	Results
HTRB	Ta=150C,80% Rated Voltage	1008 hrs	0/160
Autoclave+PC	Ta=121C RH=100% ~15 psig	96 hrs	0/160
H3TRB+PC	Ta=85C RH=85% bias=80% rated V or100V Max	504 hrs	0/160
IOL+PC	Ta=25C, Delta TJ = 100 C, Ton/off = 2 min.	7500 cyc	0/160
TC+PC	Ta= -65 C to 150 C	1000 cyc	0/160
RSH	Ta=260C, 10 sec dwell		0/60

ELECTRICAL CHARACTERISTIC SUMMARY:

There are no changes in electrical characteristics and product performance meets data sheet Specifications. Characterization data is available upon request.

CHANGED PART IDENTIFICATION:

Affected products from ON Semiconductor with date code 1436 representing WW36, 2014 and greater may be sourced from either the Niigata Fab (Japan) or the ISMF Fab (Malaysia).

**FINAL PRODUCT/PROCESS CHANGE NOTIFICATION #20349****List of affected General Parts:**

MJF44H11G	MJE340G	MJB45H11T4G
MJB44H11G	MJE344G	MJE15029G
D44H8G	2N5657G	MJE15031G
D44VH10G	BD159G	MJF15031G
D44H11G	MJD340T4G	MJE15033G
MJB44H11T4G	MJD44H11RLG	MJE172G
MJE15032G	MJD44H11G	BD140G
BD135TG	MJD44H11T5G	BD788G
BD139G	MJD44H11-1G	MJE170G
MJE182G	MJD44H11T4G	MJE171G
BD137G	NJW0281G	BD136G
BD135G	NJL1302DG	BD138G
BD787G	NJW1302G	MJL4302AG
MJE181G	MJW1302AG	MJE350G
MJE180G	MJL1302AG	MJD45H11RLG
NJD2873T4G	D45H8G	MJD45H11-1G
2N5655G	D45VH10G	MJD45H11G
MJE3439G	D45H11G	MJD45H11T4G
MJD340RLG	MJB45H11G	NJL0302DG
MJD340G	MJF45H11G	NJW0302G
MJE5850G	MJE5851G	MJE5852G